## NSN 5961-00-810-5833

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View Online at https://aerobasegroup.com/nsn/5961-00-810-5833 **Inclosure Material:** Metal **Overall Length:** 0.344 inches **Overall Diameter:** 0.648 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact **Electrode Internally-electrically Connected To Case:** Collector **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Overall Width Across Flats:** Between 0.667 inches and 0.687 inches **Thread Size:** 0.250 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 80.0 breakdown voltage, collector-to-base, emitter open and 80.0 breakdown voltage, collector-to-emitter, base open and 8.0 breakdown voltage, emitter-to-base, collector open **Current Rating Per Characteristic:** 5.00 amperes source cutoff current **Power Rating Per Characteristic:** 60.0 watts small-signal input power, common-collector **Special Features:** Junction pattern arrangement: npn **Thread Series Designator:** Unf **Terminal Type And Quantity:** 3 tab, solder lug **Specification Data:** 80131-release3225 professional/industrial association specification Shelf Life: N/a

No

**Unit Of Measure:** 

Demilitarization:

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